

DUAL 4FF MICRO SD 3IN2 CONNECTOR

1. Introduction

1.1 Objective

Testing was performed on the DUAL 4FF MICRO SD 3IN2 CONNECTOR to determine if it meets the requirement of design objective, 108-140083

1.2 Scope

This report covers the electrical, mechanical and environment performance requirements of the DUAL 4FF MICRO SD 3IN2 CONNECTOR.

The qualification testing was performed between 11AUG2015 and 31AUG2015.

The following documents form a part of this specification to the extent specified herein. In the event of conflict between the requirements of the specification and the product drawing, the product drawing shall take precedence. In the event of conflict between the requirements of this specification and the referenced documents, this specification shall take precedence.

1.3 Conclusion

The DUAL 4FF MICRO SD 3IN2 CONNECTOR meets the electorical, mechanical and environmental performance requirements of design objective, 108-140083

1.4 Product description

The DUAL 4FF MICRO SD 3IN2 CONNECTOR is designed to make a connection between a 4FF SIM, micro SD and printed circuit board or dual 4FF SIM and printed circuit board.

1.5 Test samples

Samples were taken randomly from mass production samples. The following samples were used.

Part number	Description
2290741-1	DUAL 4FF MICRO SD 3IN2 CONNECTOR
TB-1736	Test card (4FF SIM)
TB-1942	Test card (micro SD)

Fig.1



2. Test contents

Para.	Test items	Requirements	Judgment
2.1	Examination of product	Visual inspection No physical damage	Acceptable
		Electrical requirements	
2.2	Contact resistance (low level)	 Initial contact resistance: 50mΩ Max. Contact resistance after group testing: 100mΩ Max. Contact resistance includes also the bulk resistance due to terminal After any environmental test for every contact Initial detect switch resistance: 100mΩ Max. Detect switch resistance after group testing: 200mΩ Max. Mate connector with dry circuit (20mV, 100mA Max.) at min. deflection position 4-wire measurement required (IEC 60512-2-1) 	Acceptable
2.3	Insulation resistance	 1000MΩ Min. Unmated connector with 100 VDC between adjacent contact for 1 minute (IEC 60512-3-1) 	Acceptable
2.4	Dielectric strength	 No voltage breakdown Unmated connector with 500 VAC between adjacent contact for 1 minute (IEC 60512-3-1) 	Acceptable
2.5	Temperature rise	 30°C Max. under loaded rating current (0.3A) Contacts series-, apply test current of loaded rating current of the circuit Measure the temperature rising by probing on soldered areas of contacts After the temperature becomes stabilized deduct ambient temperature from the measured 	Acceptable

Fig. 2 (Cont.)



Para.	Test items	Requirements	Judgment
		Mechanical requirements	
2.6	Tray mating force	 10N Max. Tray inserts connector without card No mechanical damage for connector Operation speed 10 mm/min. Measure the force to insert the tray in the connector 	Acceptable
2.7	Tray unmating force	 Initial : 5~10N After test : 3N Min. Pull out of the tray from connector without card No mechanical damage for connector Operation speed 10 mm/min. Measure the pull out force from connector 	Acceptable
2.8	Tray push out force	 14N MAX. No mechanical damage for connector Operation speed 10 mm/min. Measure the maximum force during tray ejection operation without card 	Acceptable
2.9	Durability	 Contact resistance: 100mΩ Max. Detect switch resistance: 200mΩ Max. No mechanical damage for connector Mating contacts at 500 cycles/hour, including pause between mate/unmate to 2000 cycles After every 100 (Max.) cycles blow with dry air 	Acceptable
2.10	Vibration	 Discontinuity during testing <1µs with all contacts in series No mechanical damage No change to performance Contact resistance: 100mΩ Max. Detect switch resistance: 200mΩ Max. Frequency: 10 - 55 - 10 Hz Traversed in 1 minute amplitude 2 hours each of 6 mutually perpendicular 	Acceptable
2.11	Shock	 Discontinuity during testing <1µS with all contacts in series No mechanical damage No change to performance Contact resistance: 100mΩ Max. Detect switch resistance: 200mΩ Max. Pulse shape=half sine Peak acceleration =50G Duration of pulse=11ms Apply 3 shocks in each direction along the 3 mutually perpendicular axes (18 shocks) (IEC60068-2-27Ea) 	Acceptable

Fig. 2 (Cont.)



Para.	Test items	Requirements	Judgment
		Environmental requirements	
2.12	Temperature life Thermal shock	 No mechanical damage No change to performance Contact resistance: 100mΩ Max. Detect switch resistance: 200mΩ Max. +85±2°C for 96 hours; recovery period 1-2hours under ambient atmospheric conditions (IEC60068-2-2Bb) No mechanical damage 	Acceptable
		 No change to performance Contact resistance: 100mΩ Max. Detect switch resistance: 200mΩ Max. 26 cycle at T_a = -40 °C for 0.5 hours; then change of temp=25°C Max. 5 minute; then T_b=+85°C for 0.5 hours; then cool to ambient Recovery: 2 hours at ambient atmosphere 	Acceptable
2.14	Humidity - temperature cycling	 No change to performance Contact resistance: 100mΩ Max. Detect switch resistance: 200mΩ Max. Insulation resistance should be measured Measure the resistance without opening the mating after test Temp 25-65°C, RH 90-95% for 10 cycles Cold shock -10°C performed (EIA-364-31) 	Acceptable
2.15	Salt spray	 No mechanical damage No change to performance Contact resistance: 100mΩ Max. Detect switch resistance: 200mΩ Max. Temp: 35±2°C RH 90 - 95% Concentration: 5±1% (PH 6.5 - 7.2) Operating time: 48 hours 	Acceptable
2.16	Solderability	 No mechanical damage No change to performance Solderable area shall have a minimum 95% solder Peak temperature 240°C Reflow time(230°C MIN): 25~50 seconds 	Acceptable

Fig. 2 (Cont.)



Para.	Test items	Requirements	Judgment
		Environmental requirements	
2.17	Resistance to reflow heat	 No mechanical damage No change to performance Temp. ('C) 240-248 230 217 165 70-90 45-80 Time (Sec) 	Acceptable
2.18	Resistance to loading force on slider	 No mechanical damage No change to performance Fix the tray after tray insertion to the connector. Push the slider with 40N force and hold on for 15 seconds. 	Acceptable

Fig. 2 (End)



3. Product qualification test sequence

						Test	Group			
Para.	Test Examination	1	2	3	4	5	6	7	8	9
					Test S	Sequen	ice (a)			
2.5.1	Examination of product	1,11	1,7	1,5	1,3	1,3	1,12	1,9	1,8	1,4
2.5.2	Contact resistance (low level)	2,7	2,4,6	2,4			2,8		2,5,7	
2.5.3	Insulation resistance							2,7		
2.5.4	Dielectric withstanding voltage							3,8		
2.5.5	Temperature rise					2				
2.5.6	Tray mating force	3,8					3,9			
2.5.7	Tray unmating force	4,9					4,10			
2.5.8	Tray push out force	5,10					5,11			
2.5.9	Durability	6					6	4	3	
2.5.10	Vibration		3							
2.5.11	Shock		5							
2.5.12	Temperature life						7	5	4	
2.5.13	Thermal shock							6	6	
2.5.14	Humidity-temperature cycling									
2.5.15	Salt spray			3						
2.5.16	Solderability				2					
2.5.17	Resistance to Reflow heat									2
2.5.18	Resistance to loading force on slider									3

(a) Numbers indicate sequence in which the tests are performed.

Fig. 3



4. Test result summary

Test item		l Init			Resu	lt		Requirements	Judge
		01110	Ν	Max.	Min.	Ave.	Sig.	rioquiromonito	-ment
		1		Te	st group	1		Γ	
Examination of produc	t	-	3	No abr	normaliti	es		No abnormalities	Accept -able
Contact registeres	4FF		18	18.50	8.97	12.31	4.39	Contact : 50mΩ Max.(initial) Detect switch : 100mΩ Max.(initial)	Accept -able
(Low level)	micro SD	mΩ	24	11.85	9.57	10.36	0.64		Accept -able
	Detect switch		3	14.03	11.83	12.58	1.26		Accept -able
Tray mating force		Ν	3	4.7	4.3	4.53	0.21	10N Max.	Accept -able
Tray unmating force		Ν	3	6.9	6.3	6.67	0.32	5~10N	Accept -able
Tray push out force		Ν	3	10.5	8.9	9.66	0.77	14N Max.	Accept -able
Contact resistance	4FF		18	18.85	9.25	13.49	3.64	Contact	Accept -able
(Low level)	micro SD	mΩ	24	13.27	9.61	10.92	1.06	: 100mΩ Max.(final) Detect switch	Accept -able
	Detect switch		3	19.07	13.87	17.17	2.87	: 200mΩ Max.(final)	Accept -able
Tray mating force		Ν	3	3.5	3.5	3.50	0.00	10N Max.	Accept -able
Tray unmating force		Ν	3	4.8	4.6	4.70	0.10	3N Min.	Accept -able
Tray push out force		Ν	3	6.7	6.7 6.0 6.42 0.41		0.41	14N Max.	Accept -able
Examination of produce after test	t	-	3	No abr	normaliti	es		No abnormalities	Accept -able

Group 1 (End)



Test item		Unit			Resu	lt		Requirements	Judge
			Ν	Max.	Min.	Ave.	Sig.		-ment
				Tes	st group	2			
Examination of produc	t	-	3	No abnormalities				No abnormalities	Accept -able
Contact resistance (Low level) Initial	4FF		18	18.53	8.23	11.75	4.43	Contact	Accept -able
	micro SD	mΩ	24	12.81	9.50	10.16	0.88	: 50mΩ Max.(initial) Detect switch : 100mΩ Max.(initial)	Accept -able
	Detect switch		3	22.15	13.73	16.75	4.68		Accept -able
Vibration		-	3	No abr	normaliti	es		1µs Max.	Accept -able
0	4FF		18	18.29	8.19	11.68	4.41	Contact : 100mΩ Max. Detect switch : 200mΩ Max.	Accept -able
(Low level)	micro SD	mΩ	24	10.70	9.40	9.92	0.45		Accept -able
	Detect switch		3	33.06	26.91	29.15	3.40		Accept -able
Shock		-	3	No abr	normaliti	es		1µs Max.	Accept -able
Contact registeres	4FF		18	18.23	7.93	11.64	4.37	Contact	Accept -able
(Low level)	micro SD	mΩ	24	10.65	9.52	10.02	0.45	: 100mΩ Max.(final) Detect switch	Accept -able
aller Shock	Detect switch		3	61.05	47.02	55.78	7.64	: 200mΩ Max.(final)	Accept -able
Examination of produc	t	-	3	No abr	normaliti	es		No abnormalities	Accept -able

Test item		Unit			Resu	lt		Requirements	Judge
			Ν	Max.	Min.	Ave.	Sig.		-ment
				Tes	st group	3			
Examination of product			3 No abnormalities					No abnormalities	Accept -able
Contact resistance (Low level)	4FF	mΩ	18	18.52	8.98	12.23	4.49	Contact	Accept -able
	micro SD		24	10.59	9.47	9.89	0.32	: 50mΩ Max.(initial) Detect switch : 100mΩ Max.(initial)	Accept -able
mina	Detect switch		3	14.92	10.25	12.17	2.44		Accept -able
Contact registered	4FF		18	30.67	11.52	17.75	6.23	Contact	Accept -able
(Low level)	micro SD	mΩ	24	22.03	11.16	14.72	3.39	: 100mΩ Max.(final) Detect switch	Accept -able
aner san spray	Detect switch		3	50.83	41.10	46.40	4.92	: 200mΩ Max.(final)	Accept -able
Examination of produc	t	-	3	No abr	normaliti	es		No abnormalities	Accept -able

Group 2,3 (End)



Test item	Unit	N	Result	Requirements	Judge -ment					
Test group 4										
Examination of product	-	3	No abnormalities	No abnormalities	Accept -able					
Solderability	-	3	More than 95% of tested area was covered with wet solder	Minimum 95% solder	Accept -able					
Examination of product after test	-	3	No abnormalities	No abnormalities	Accept -able					

Test item					Resu	lt		Requirements	Judge
		01	Ν	Max.	Min.	Ave.	Sig.	riequiremente	-ment
				Tes	st group	5			
Examination of produc	ct	- 3 No abnormalities				No abnormalities	Accept -able		
Temperature rise	4FF		3	1.8	1.2	1.45	0.18	30°C Max.	Accept -able
	micro SD		3	2.2	1.4	1.77	0.26		Accept -able
Examination of product after temperature rise		-	3	No abr	normaliti	es		No abnormalities	Accept -able

Group 4,5 (End)



Test item		Unit			Resu	lt	0.	Requirements	Judge
			Ν	Max.	Min. st aroun	Ave.	Sig.		-mem
Examination of product			3	No abnormalities				No abnormalities	Accept -able
Contact resistance (Low level) Initial	4FF		18	19.31	8.52	12.43	4.60	Contact	Accept -able
	micro SD	mΩ	24	15.90	9.37	10.63	1.68	: 50mΩ Max.(initial) Detect switch	Accept -able
	Detect switch		3	12.54	11.19	11.66	0.76	: 100mΩ Max.(initial)	Accept -able
Tray mating force		Ν	3	5.2	4.1	4.57	0.57	10N Max.	Accept -able
Tray unmating force		Ν	3	6.7	6.4	6.60	0.17	5~10N	Accept -able
Tray push out force		Ν	3	9.4	8.7	9.05	0.33	14N Max.	Accept -able
Contact registered	4FF		18	26.01	11.67	18.30	5.04	Contact : 100mΩ Max. Detect switch : 200mΩ Max.	Accept -able
(Low level)	micro SD	mΩ	24	28.01	10.82	16.10	5.17		Accept -able
aner durability	Detect switch		3	66.58	49.47	58.42	8.58		Accept -able
Contact registered	4FF		18	31.38	10.61	20.90	7.80	Contact	Accept -able
(Low level)	micro SD	mΩ	24	29.68	9.98	15.81	5.30	: 100mΩ Max.(final) Detect switch	Accept -able
	Detect switch		3	69.82	54.18	62.02	7.82	: 200mΩ Max.(final)	Accept -able
Tray mating force		Ν	3	3.5	3.3	3.43	0.12	10N Max.	Accept -able
Tray unmating force		Ν	3	4.8	4.1	4.40	0.36	3N Min.	Accept -able
Tray push out force		Ν	3	7.2	5.7	6.20	0.89	14N Max.	Accept -able
Examination of produc after test	t	-	3	No abr	normaliti	es		No abnormalities	Accept -able

Group 6 (End)



Qualification test report

Test item	Unit		Resu	t	Requirements	Judge			
		Ν	Max. Min.	Ave.	Sig.	i lequi emente	-ment		
Test group 7									
Examination of product	-	3	No abnormaliti	es		No abnormalities	Accept -able		
Insulation resistance	MΩ	3	19900 Min.			1000MΩ Min.	Accept -able		
Dielectric withstanding voltage	-	3	No voltage bre	akdown		No voltage breakdown	Accept -able		
Insulation resistance	MΩ	3	3230 Min.			1000MΩ Min.	Accept -able		
Dielectric withstanding voltage	-	3	No voltage bre	akdown		No voltage breakdown	Accept -able		
Examination of product after test		3	No abnormaliti	es		No abnormalities	Accept -able		

$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	Test item		Unit	Result				Requirements	Judge	
$ \begin{array}{ c c c c c c c } \hline \mbox{Test group 8} \\ \hline \mbox{Examination of product} & - & 3 & \mbox{No abnormalities} & \mbox{No abnormalities} & \mbox{No abnormalities} & \mbox{No abnormalities} & \mbox{Accept} & -able $			01111	Ν	Max.	Min.	Ave.	Sig.	rioquironionio	-ment
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Test group 8									
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Examination of product		-	3	No abnormalities		No abnormalities	Accept -able		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Contact resistance (Low level) Initial	4FF	mΩ	18	18.72	8.74	12.06	4.45	Contact : 50mΩ Max.(initial) Detect switch : 100mΩ Max.(initial)	Accept -able
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$		micro SD		24	10.89	9.52	10.25	0.47		Accept -able
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $		Detect switch		3	20.04	12.16	15.72	4.00		Accept -able
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Contact resistance (Low level) after durability and thermal shock	4FF	mΩ	18	18.81	9.24	12.68	4.23	Contact : 100mΩ Max. Detect switch : 200mΩ Max.	Accept -able
thermal shockDetect switch3 60.31 43.74 51.76 8.30 : $200m\Omega$ Max.Accept -ableContact resistance (Low level) after humidity-temperatur e cycling4FF18 18.46 9.13 12.51 4.27 Contact : $100m\Omega$ Max.(final) Detect switchAccept -ableDetect switch $m\Omega$ 24 17.72 9.52 11.40 2.22 Contact : $100m\Omega$ Max.(final) Detect switch : $200m\Omega$ Max.(final)Accept -ableExamination of product after test-3No abnormalitiesNo abnormalitiesAccept -able		micro SD		24	11.91	9.46	10.43	0.83		Accept -able
Contact resistance (Low level) after humidity-temperatur e cycling4FF1818.469.1312.514.27Contact - 3Accept -able1818.469.1312.514.27Contact : 100mΩ Max.(final) Detect switch : 200mΩ Max.(final)Accept 		Detect switch		3	60.31	43.74	51.76	8.30		Accept -able
Accept after humidity-temperatur e cyclingmicro SDmΩ2417.729.5211.402.22: 100mΩ Max.(final) Detect switch : 200mΩ Max.(final)Accept -ableExamination of product 	Contact resistance (Low level) after r humidity-temperatur e cycling	4FF	mΩ	18	18.46	9.13	12.51	4.27	Contact : 100mΩ Max.(final) Detect switch : 200mΩ Max.(final)	Accept -able
Humanity temperator e cyclingDetect switch339.5631.8035.813.89: 200mΩ Max.(final)Accept -ableExamination of product after test-3No abnormalitiesNo abnormalitiesAccept -able		micro SD		24	17.72	9.52	11.40	2.22		Accept -able
Examination of product after test-3No abnormalitiesAccept -able		Detect switch		3	39.56	31.80	35.81	3.89		Accept -able
	Examination of product after test		-	3	No abnormalities		No abnormalities	Accept -able		

Group 7,8 (End)



Test item	Unit	N	Result	Requirements	Judge -ment				
Test group 9									
Examination of product	-	3	No abnormalities	No abnormalities	Accept -able				
Resistance to reflow heat	-	3	No mechanical damage	No mechanical damage	Accept -able				
Resistance to loading force on slider	-	3	No mechanical damage	No mechanical damage	Accept -able				
Examination of product after test	-	3	No abnormalities	No abnormalities	Accept -able				

Group 8 (End)